

## N-channel 800 V, 1.3 $\Omega$ typ., 4.5 A MDmesh™ K5 Power MOSFETs in TO-220FP and I<sup>2</sup>PAKFP packages

Datasheet - production data

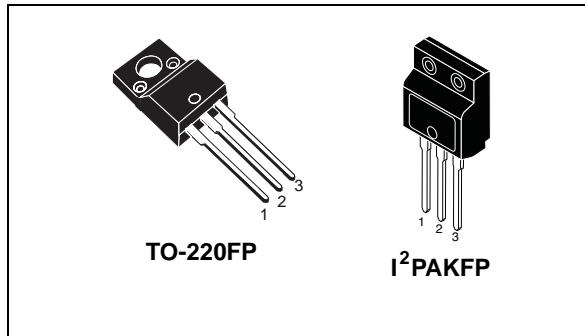
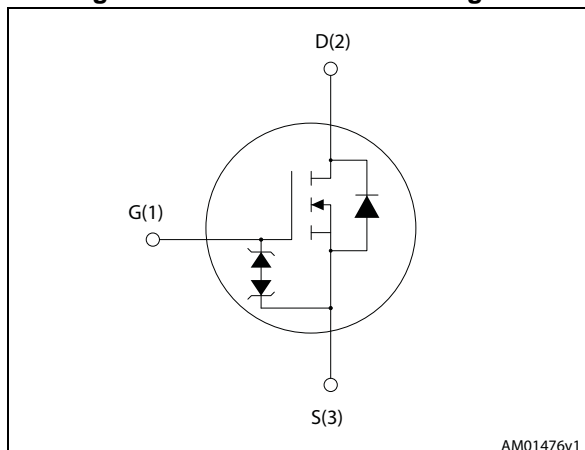


Figure 1. Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>	P <sub>TOT</sub>
STF6N80K5	800 V	1.6 $\Omega$	4.5 A	25 W
STFI6N80K5				

- Industry's lowest R<sub>DS(on)</sub>
- Industry's best figure of merit (FoM)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

These very high voltage N-channel Power MOSFETs are designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1. Device summary

Order code	Marking	Package	Packing
STF6N80K5	6N80K5	TO-220FP	Tube
STFI6N80K5		I <sup>2</sup> PAKFP	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate- source voltage	30	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	4.5 <sup>(1)</sup>	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	2.8	A
$I_{DM}^{(2)}$	Drain current (pulsed)	18	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	25	W
$I_{AR}$	Max current during repetitive or single pulse avalanche (pulse width limited by $T_{jmax}$ )	1.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$ , $I_D = I_{AS}$ , $V_{DD} = 50\text{ V}$ )	85	mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ , $T_C = 25\text{ °C}$ )	2500	V
$T_J$	Operating junction temperature range	-55 to 150	°C
$T_{stg}$	Storage temperature range		

- Limited by maximum junction temperature
- Pulse width limited by safe operating area
- $I_{SD} \leq 4.5\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ , peak  $V_{DS} \leq V_{(BR)DSS}$
- $V_{DS} \leq 640\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	5	°C/W
$R_{thj-amb}$	Thermal resistance junction-amb	62.5	

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified).

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 1\text{ mA}$	800			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 800\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 800\text{ V}$ , $T_j = 125\text{ °C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$		1.3	1.6	$\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	270	-	pF
$C_{oss}$	Output capacitance		-	25	-	pF
$C_{riss}$	Reverse transfer capacitance		-	0.7	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0$ , $V_{DS} = \text{from } 0 \text{ to } 640\text{ V}$	-	38	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	16	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0$	-	7.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 640\text{ V}$ , $I_D = 4.5\text{ A}$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15: Gate charge test circuit</a> )	-	13	-	nC
$Q_{gs}$	Gate-source charge		-	2.1	-	nC
$Q_{gd}$	Gate-drain charge		-	9.6	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$ , $I_D = 2.25\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14: Switching times test circuit for resistive load</a> and <a href="#">Figure 19: Switching time waveform</a> )	-	16	-	ns
$t_r$	Rise time		-	7.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	28.5	-	ns
$t_f$	Fall time		-	16	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		4.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		18	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4.5\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 4.5\text{ A}$ , $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ , (see <a href="#">Figure 16: Test circuit for inductive load switching and diode recovery times</a> )	-	280		ns
$Q_{rr}$	Reverse recovery charge		-	2.2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	15.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 4.5\text{ A}$ , $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 16: Test circuit for inductive load switching and diode recovery times</a> )	-	450		ns
$Q_{rr}$	Reverse recovery charge		-	3.15		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	14		A

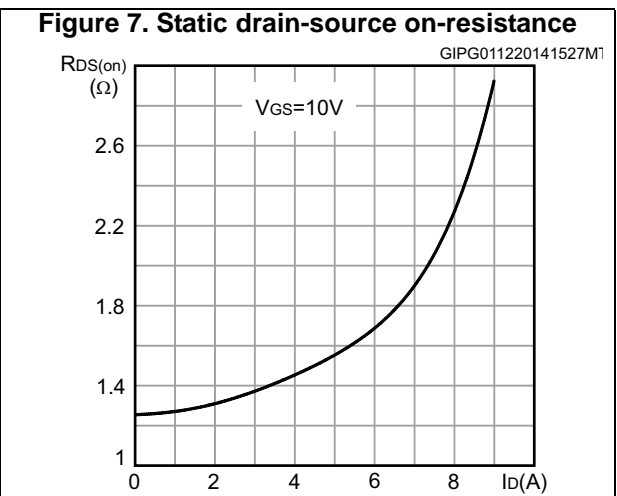
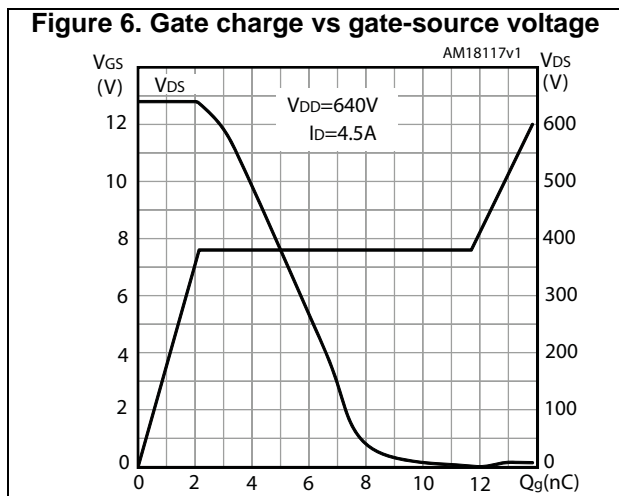
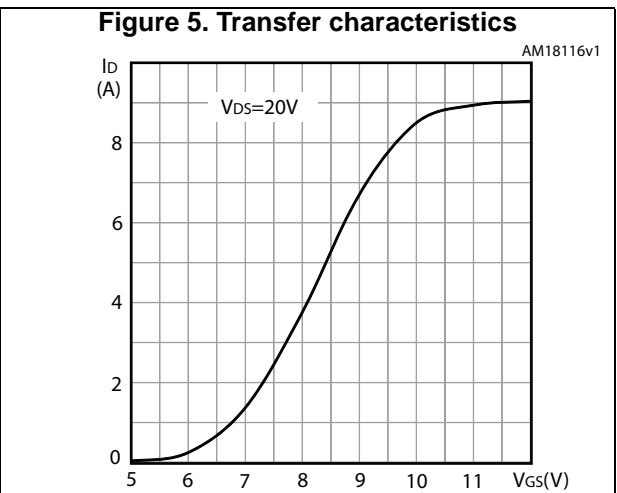
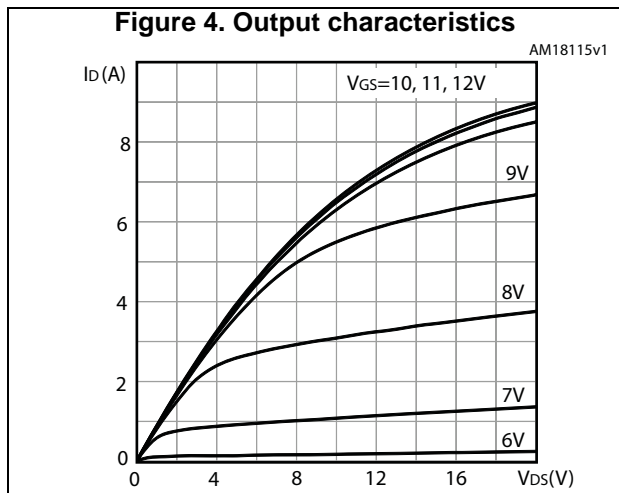
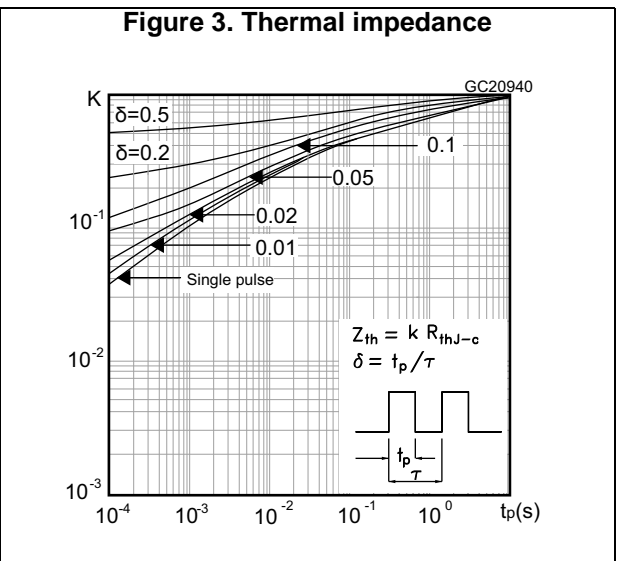
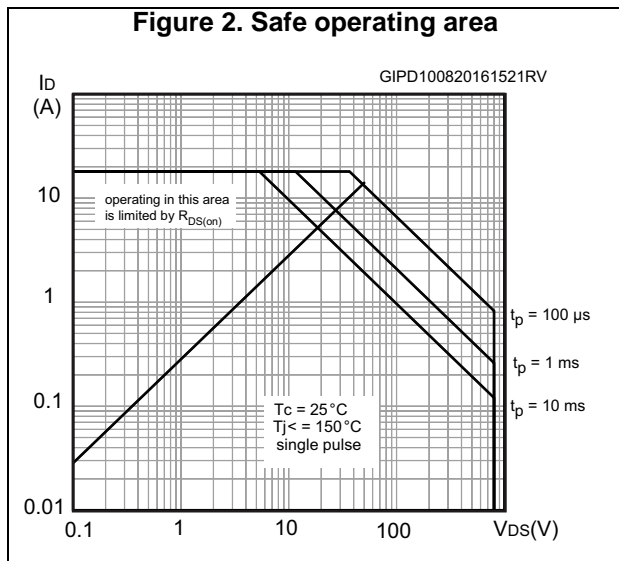
1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

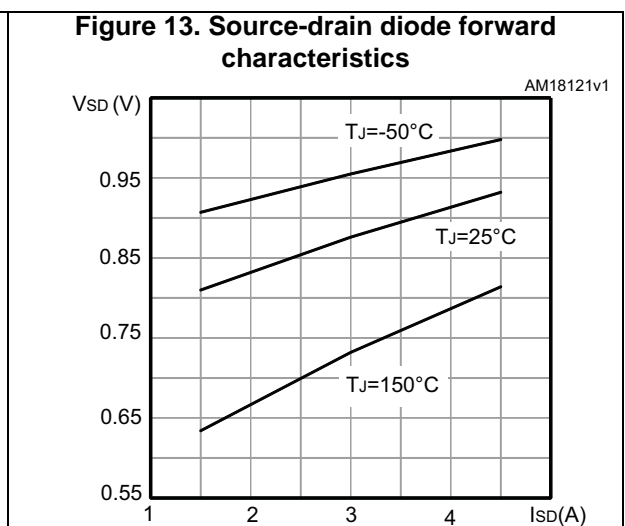
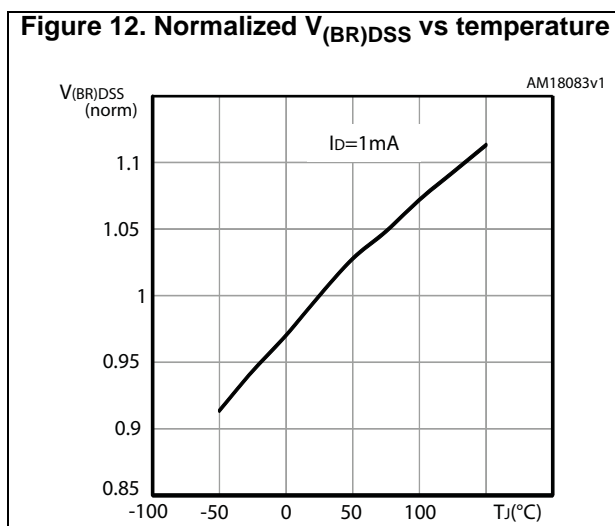
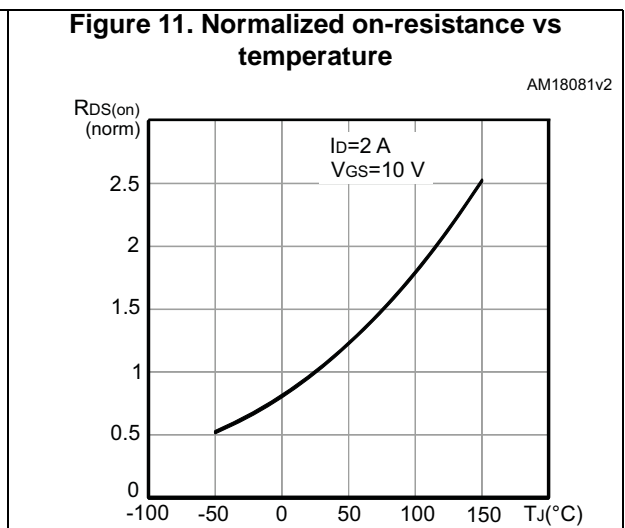
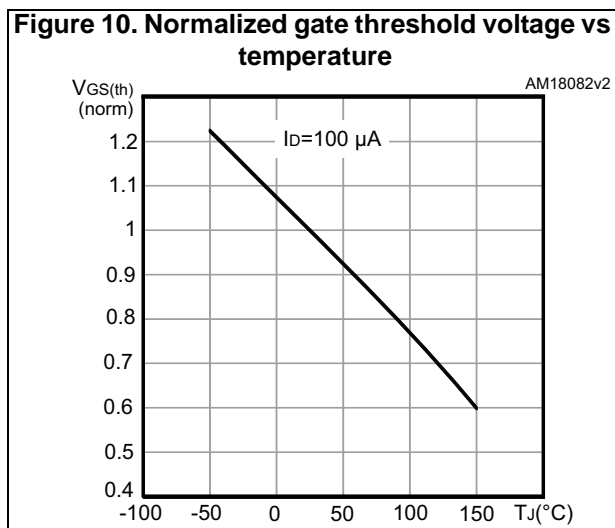
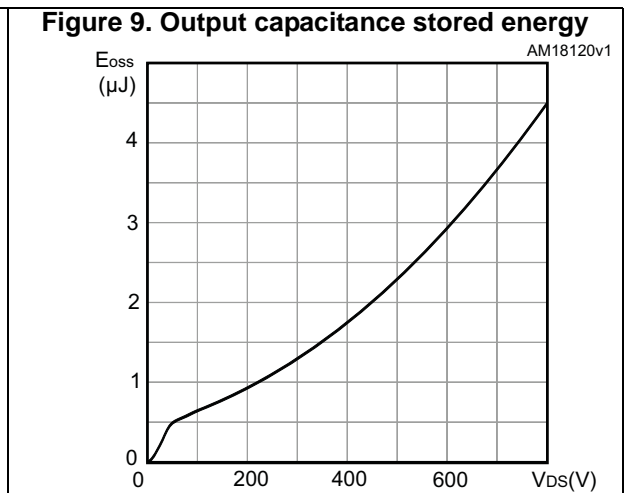
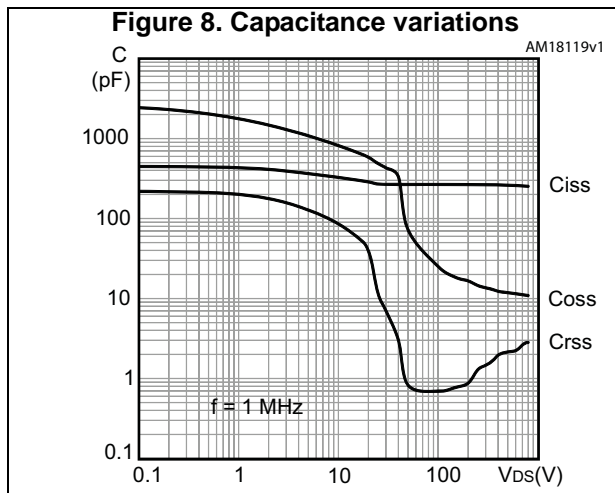
Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0$	30	-	-	V

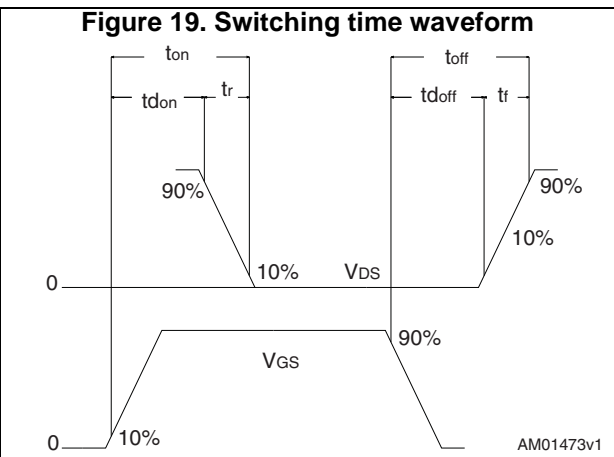
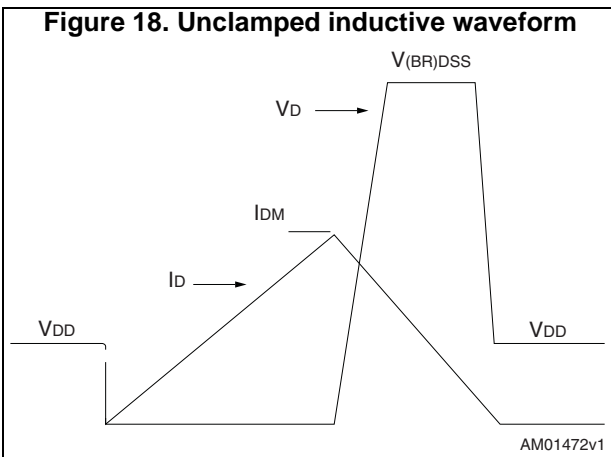
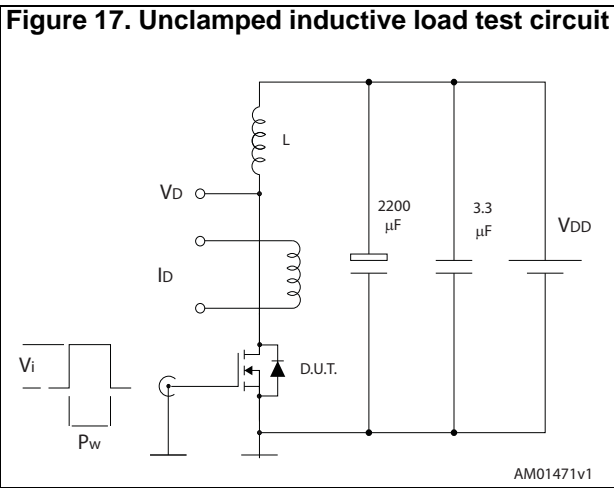
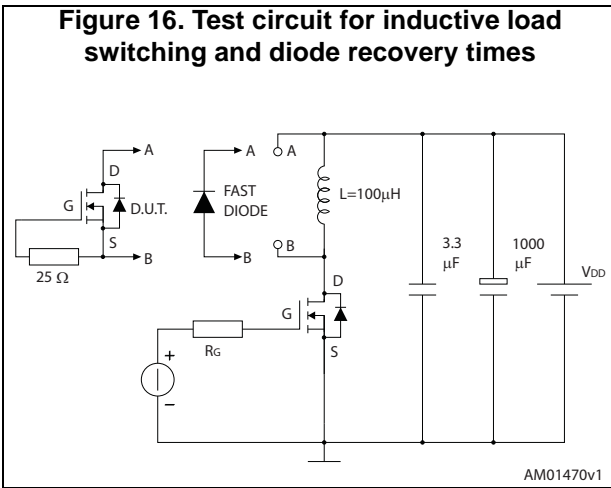
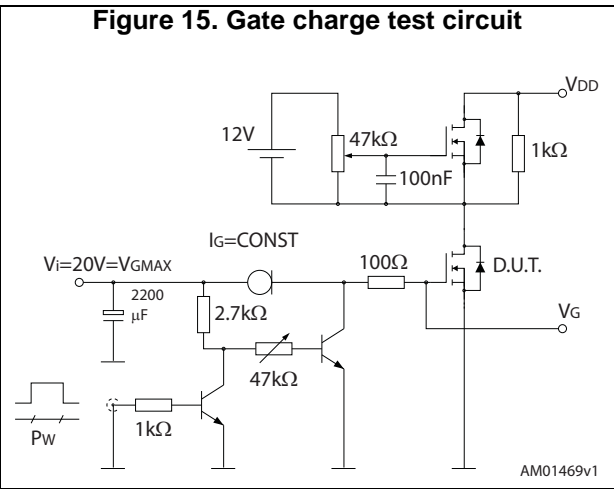
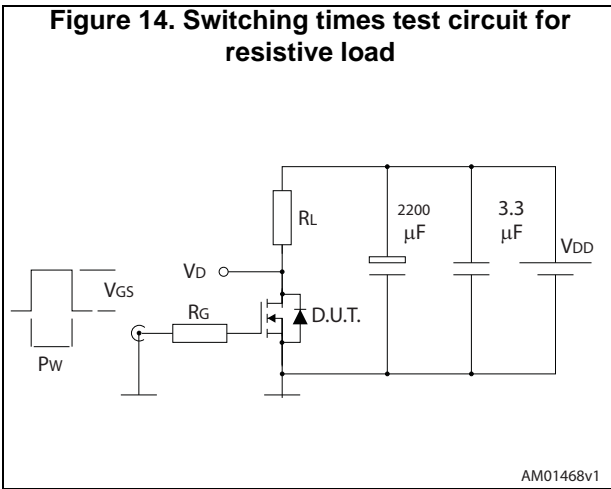
The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)





### 3 Test circuits





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 TO-220FP package information

Figure 20. TO-220FP package outline

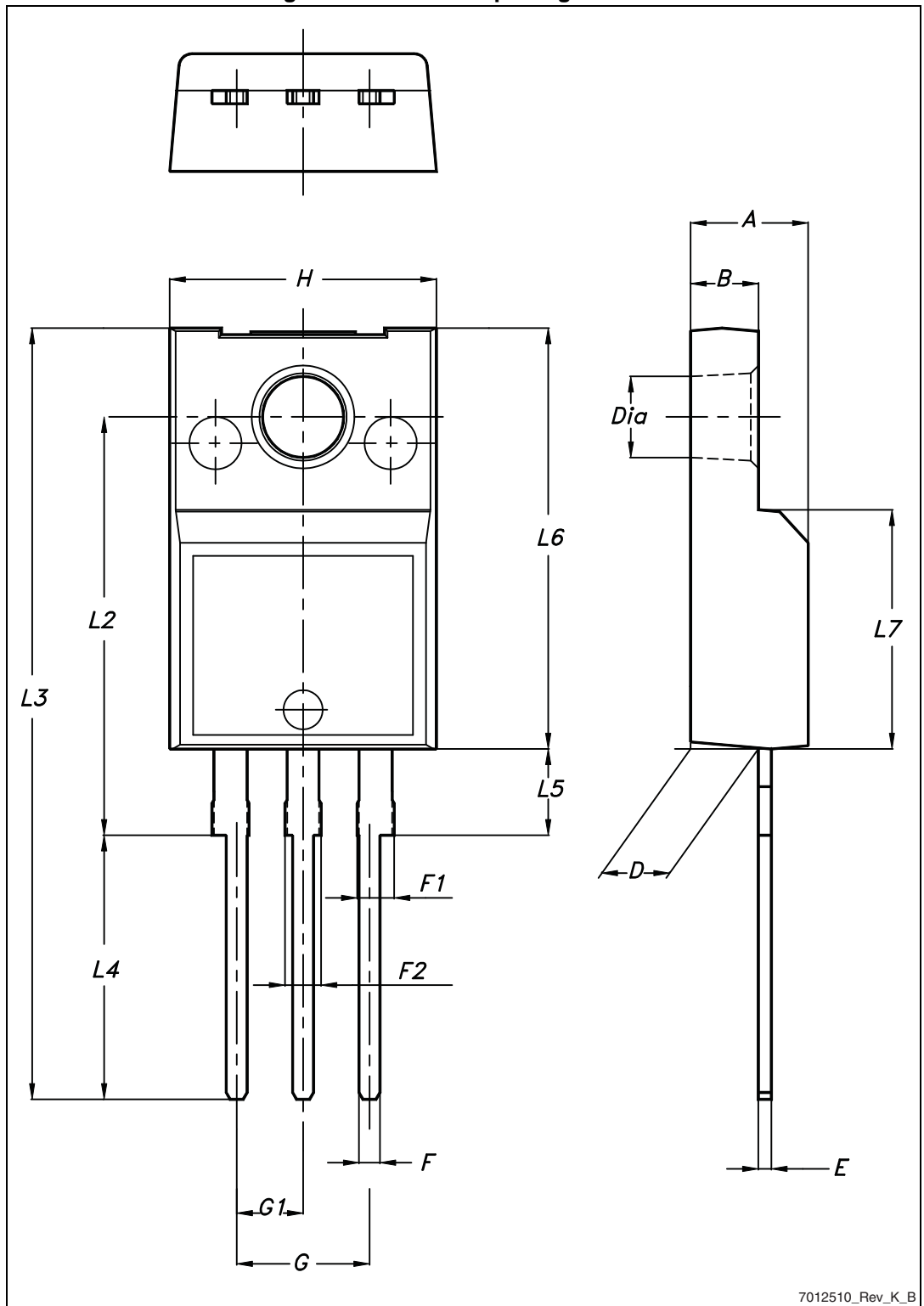


Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

## 4.2 I<sup>2</sup>PAKFP (TO-281) package information

Figure 21. I<sup>2</sup>PAKFP (TO-281) package outline

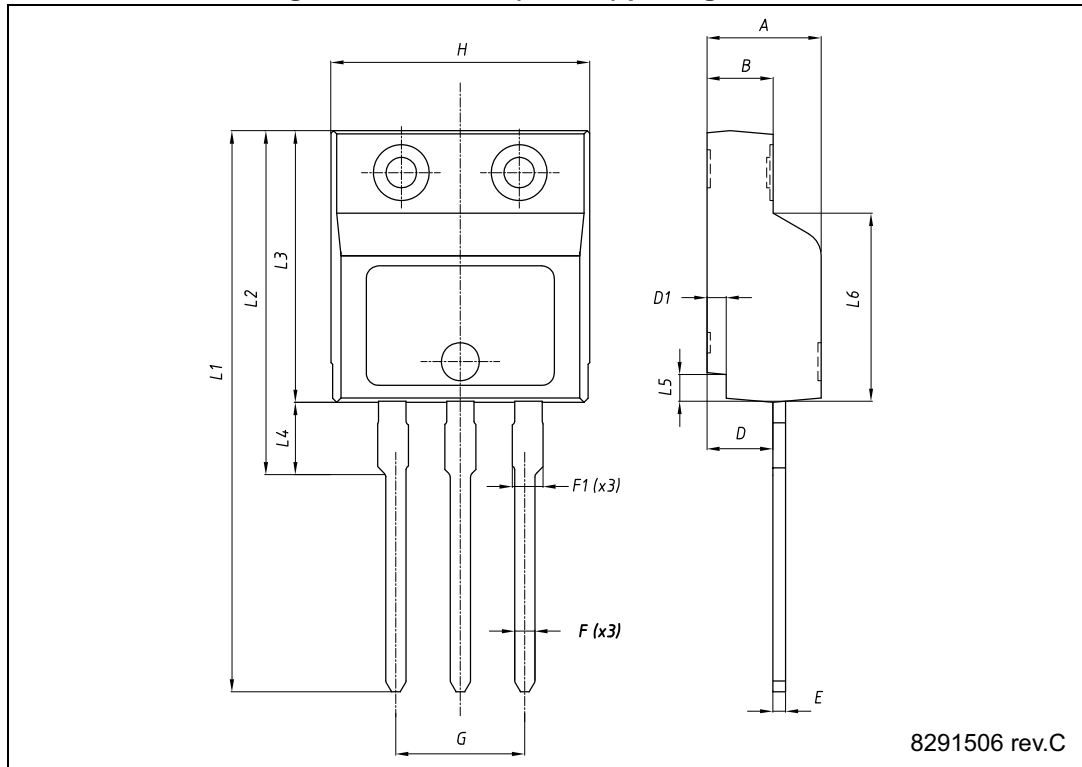


Table 10. I<sup>2</sup>PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	-	4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95		5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.50	7.60	7.70

## 5 Revision history

Table 11. Document revision history

Date	Revision	Changes
28-May-2013	1	First release.
05-Mar-2014	2	<ul style="list-style-type: none"> <li>– Datasheet status promoted from preliminary data to production data</li> <li>– Added: I<sup>2</sup>PAKFP package</li> <li>– Modified: E<sub>AS</sub> value in <i>Table 2</i></li> <li>– Added: MOSFET dv/dt ruggedness test condition and <i>note 4</i> in <i>Table 2</i></li> <li>– Modified: R<sub>G</sub> value in <i>Table 5</i></li> <li>– Modified: the entire typical values in <i>Table 5, 6 and 7</i></li> <li>– Added: <i>Section 2.1: Electrical characteristics (curves)</i></li> <li>– Minor text changes</li> </ul>
05-Dec-2014	3	<p>Updated title, features and description in cover page.</p> <p>Updated <i>Section 2.1: Electrical characteristics (curves)</i> and <i>Section 4: Package information</i>.</p> <p>Minor text changes.</p>
06-Sept-2016	4	<p>Updated <i>Table 2: Absolute maximum ratings</i>, <i>Table 4: On/off states</i>, <i>Table 5: Dynamic</i>, <i>Table 6: Switching times</i>, and <i>Table 7: Source drain diode</i>.</p> <p>Updated <i>Figure 2: Safe operating area</i> and <i>Figure 3: Thermal impedance</i>.</p> <p>Minor text changes.</p>

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